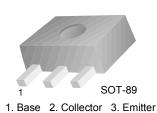
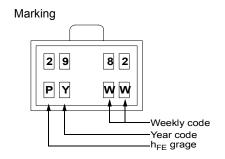


# **KSC2982 NPN Epitaxial Silicon Transistor**

### Strobe Flash & Medium Power Amplifier

- Excellent h<sub>FE</sub> Linearity : h<sub>FE1</sub>=140 ~ 600
- Low Collector-Emitter Saturation Voltage : V<sub>CE</sub>(sat)=0.5V
- Collector Dissipation : P<sub>C</sub>=1~2W in Mounted on Ceramic Board





# Absolute Maximum Ratings T<sub>a</sub> = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	30	V
V <sub>CES</sub>	Collector-Emitter Voltage	30	V
V <sub>CEO</sub>	Collector-Emitter Voltage	10	V
V <sub>EBO</sub>	Emitter Base Voltage	6	V
I <sub>C</sub>	Collector Current (DC)	2	А
I <sub>CP</sub>	Collector Current (Pulse) *	4	A
I <sub>B</sub>	Base Current (DC)	0.4	A
I <sub>BP</sub>	Base Current (Pulse) *	0.8	Α
P <sub>C</sub> P <sub>C</sub> *	Collector Power Dissipation	500 1,000	mW mW
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	-55 ~ 150	°C

<sup>\*</sup> PW  $\leq$  10ms, Duty Cycle  $\leq$  30%

Mounted on Ceramic Board (250mm<sup>2</sup> x 0.8mm)

# Electrical Characteristics T<sub>a</sub> = 25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10mA, I <sub>B</sub> = 0	10			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 1mA, I <sub>C</sub> = 0	6			V
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB} = 30V, I_{E} = 0$			100	nA
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{BE} = 6V, I_{C} = 0$			100	nA
h <sub>FE1</sub>	DC Current Gain	$V_{CE} = 1V, I_{C} = 0.5A$	140		600	
h <sub>FE2</sub>		$V_{CE} = 1V$ , $I_C = 2A$	70	140		
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	$I_C = 2A, I_B = 50mA$		0.2	0.5	V
V <sub>BE</sub> (on)	Base-Emitter On Voltage	$V_{CE}$ = 1V, $I_C$ = 2A		0.86	1.5	V
f <sub>T</sub>	Current Gain Bandwidth Product	$V_{CE}$ = 1V, $I_C$ = 2A		150		MHz
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> = 10V, I <sub>E</sub> = 0, f = 1MHz		27		pF

# **h**<sub>FE</sub> Classification

Classification	Α	В	С	D
h <sub>FE1</sub>	140 ~ 240	200 ~ 330	300 ~ 450	420 ~ 600

# **Package Marking and Ordering Information**

<b>Device Marking</b>	Device	Package	Reel Size	Tape Width	Quantity
2982	KSC2982	SOT-89	13"	-	4,000

### **Typical Performance Characteristics**

Figure 1. Static Characteristic

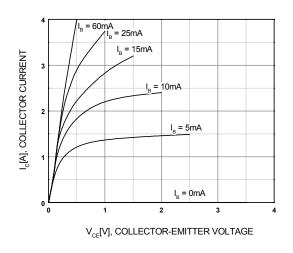


Figure 2. DC Current Gain

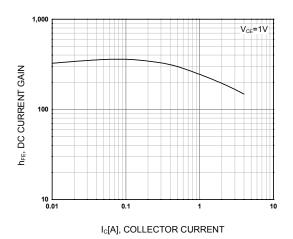
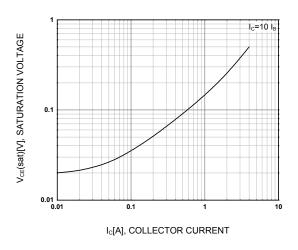


Figure 3. DCollector-Emitter Saturation Voltage Figure 4. Base-Emitter On Voltage



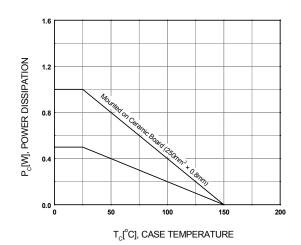


Figure 5. Safe Operating Area

KSC2982 Rev. B3

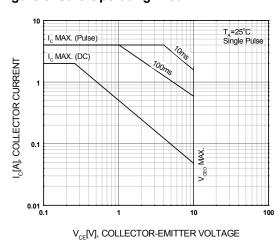
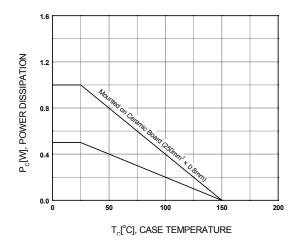


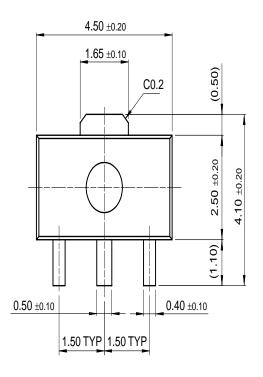
Figure 6. Power Derating

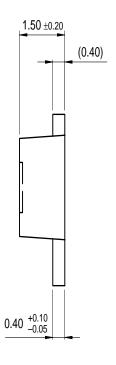


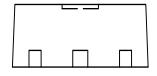
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# **Mechanical Dimensions**

# **SOT-89**







**Dimensions in Millimeters** 

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SuperSOT™-6

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### **Definition of Terms**

Datasheet Identification	Product Status	Definition
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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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